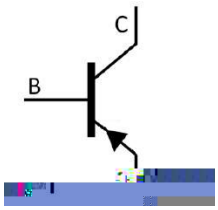
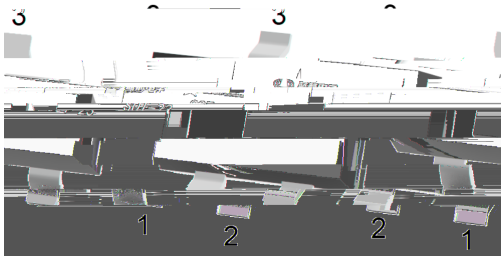
9 5 : .> / / x 6 4 6 ! - } â ’ož Silicon PNP transistor in a SOT-23 Plastic Package.

(8 9 3 7 ; m k … ` ' +) 7 ö Õ ä U ´ Å } L k —)í D }ož
Complementary pair with BRS8050MQ, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

9 ä y Ý è k á V ñ • } Ložž
Power amplifier applications, Meet the stringent requirements of automotive applications.



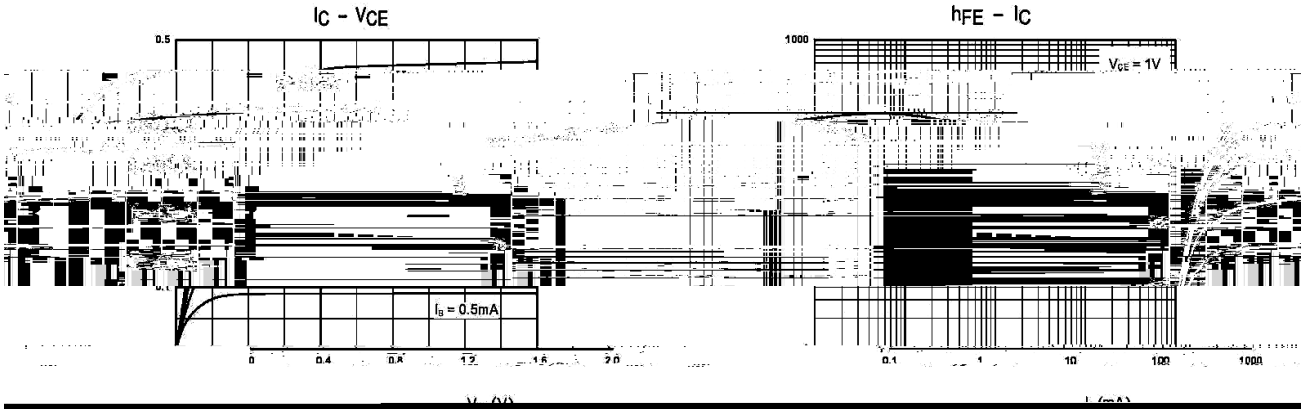


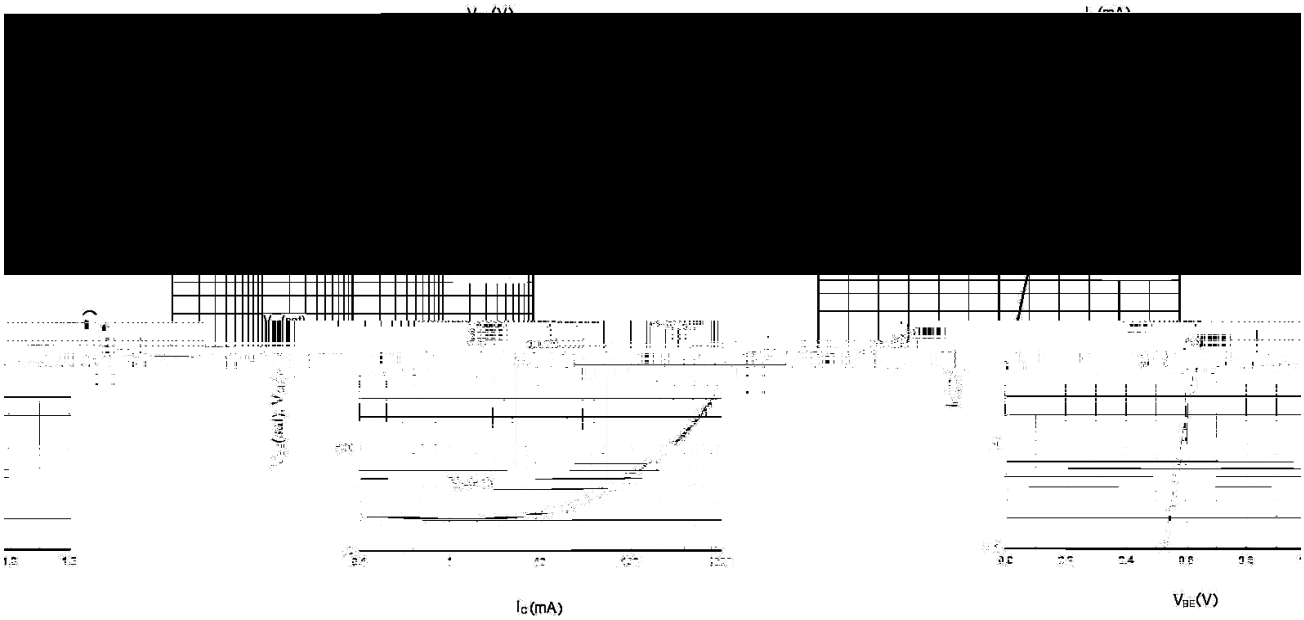
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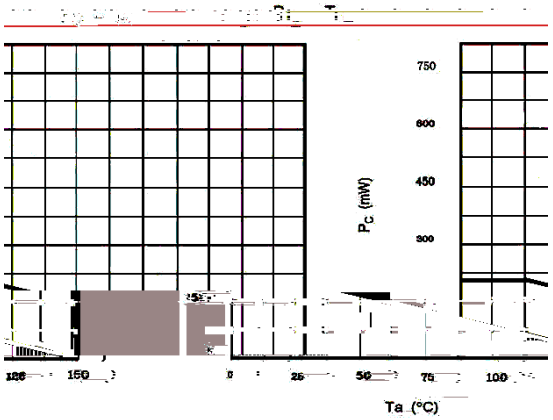
@ ƒ Parameter	… Z Symbol	ƒ › Rating	% y Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-25	V
Emitter to Base Voltage	V_{EBO}	-6.0	V
Collector Current	I_C	-800	mA
Base Current	I_B	-200	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	

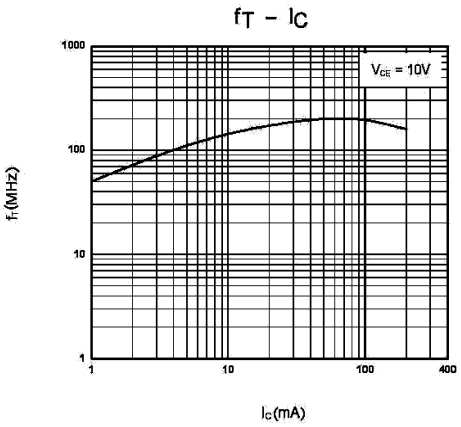
@ ƒ Parameter	… Z Symbol	y ¡ Ú ^ Test Conditions	Â 4 › Min	Á º › Typ	Â Ý › Max	% y Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=-0.1mA I_E=0	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=-2.0mA I_B=0	-25			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=-0.1mA I_C=0	-6.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=-35V I_E=0			-0.1	A
Emitter Cut-Off Current	I_{EBO}	V_{EB}=-6.0V I_C=0			-0.1	A

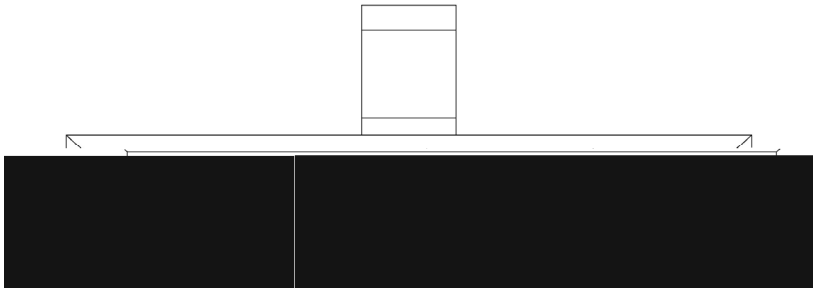
Ô ? d • Ž ¢ / Electrical Characteristic Curve











š WD t ... • Ž ¢ (x /) / : K S V K X G Z [X K 6 X U L O R K L U X / 8 8 K L R U] 9 U R J K X O T M 6

ª ¢ y

1o• Ä ½ “ † 150 ½200 - k ž • 60 ½120sec;

2o• Q › “ † 255 r 5 - k ž • 4 Ò 5 r 0.5sec;

3o•D N ò i Ò 0 , † 2 ½10 - /sec.

Note:

1.Preheating:150~200 - , Time:60~120sec.

2.Peak Temp.:255 r 5 - , Duration:5 r 0.5sec.

3. Cooling Speed: 2~10 - /sec.

ÂD /Cã p ¯ »] / Resistance to Soldering Heat Test Conditions

“ † y 260 r 5 -	ž • y 10 r 1 sec.	Temp.:260±5	Time:10±1 sec

G P á / Packaging SPEC.

2 & x / REEL

Package Type 7>û ˜ E	Units/Reel / --	Units ;>û ¦H	Dimension ;>û p . (unit ÆEmm^3)